

**METHOD FOR MANUFACTURING DEVICE SUBSTRATE
WITH METAL BACK-GATE AND STRUCTURE FORMED THEREBY**

ABSTRACT OF THE DISCLOSURE

A method (and resultant structure) of forming a semiconductor device, includes
5 forming a metal-back-gate over a substrate and a metal back-gate, forming a passivation
layer on the metal back-gate to prevent the metal back-gate from reacting with radical
species, and providing an intermediate gluing layer between the substrate and the metal
back-gate to enhance adhesion.

03617420-032704